

**KS54AHCT 564  
KS74AHCT 564****Octal D-Type Flip-Flops  
with 3-State Outputs**

T-46-07-05

**FEATURES**

- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ( $I_{OL} = 24\text{mA}$  @  $V_{OL} = 0.5\text{V}$ ) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over Industrial and military temperature ranges:  
KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$   
KS54HACT:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**DESCRIPTION**

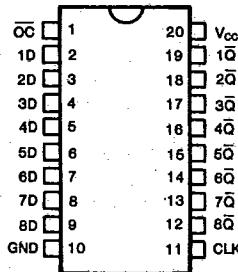
The '564 consists of 8 high-speed D-type edge-triggered flip-flops coupled to 3-state output buffers with high drive current capability. It can be used in implementing buffer registers, I/O ports, bidirectional bus driver and working registers.

The flip-flops are edge-triggered: on the positive transition of the clock, the  $\bar{Q}$  outputs are set to the complement of the logic levels that were set up at the D inputs.

The output buffers are controlled by a common signal ( $\bar{OC}$ ) which places the outputs at high impedance stat when it is taken high. The OC signal does not affect the internal operations of the flip-flops. Old data can be retained or new data can be entered while outputs are off.

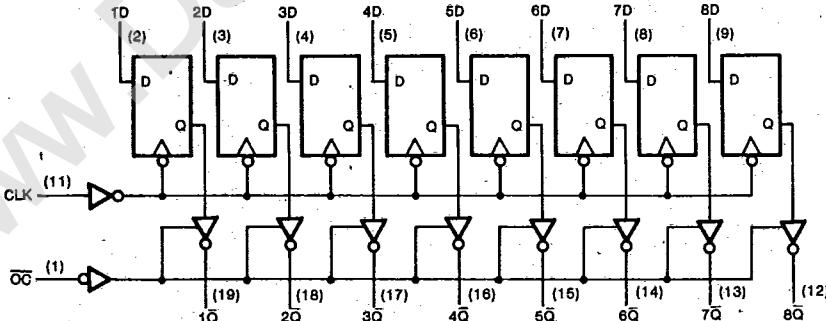
These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

**PIN CONFIGURATION****FUNCTION TABLE**

(Each Flip-Flop)

Inputs	Output		
$\bar{OC}$	CLK	D	$\bar{Q}$
L	↑	H	L
L	↑	L	H
L	L	X	$\bar{Q}_0$
H	X	X	Z

**LOGIC DIAGRAM**

SAMSUNG SEMICONDUCTOR

**KS54AHCT 564  
KS74AHCT****Octal D-Type Flip-Flops  
with 3-State Outputs**

T-46-07-05

**Absolute Maximum Ratings\***

Supply Voltage Range, V <sub>CC</sub>	.....	-0.5V to +7V
DC Input Diode Current, I <sub>IK</sub> (V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> + 0.5V)	.....	±20 mA
DC Output Diode Current, I <sub>OK</sub> (V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> + 0.5V)	.....	±20 mA
Continuous Output Current Per Pin, I <sub>O</sub> (-0.5V < V <sub>O</sub> < V <sub>CC</sub> + 0.5V)	.....	±70 mA
Continuous Current Through V <sub>CC</sub> or GND pins	.....	±250 mA
Storage Temperature Range, T <sub>STG</sub>	.....	-65°C to +150°C
Power Dissipation Per Package, P <sub>D</sub>	.....	500 mW

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
Plastic Package (N): -12mW/°C from 65°C to 85°C  
Ceramic Package (J): -12mW/°C from 100°C to 125°C

**Recommended Operating Conditions**

Supply Voltage, V <sub>CC</sub>	.....	4.5V to 5.5V
DC Input & Output Voltages*, V <sub>IN</sub> , V <sub>OUT</sub>	.....	0V to V <sub>CC</sub>
Operating Temperature Range	.....	KS74AHCT: -40°C to +85°C KS54AHCT: -55°C to +125°C
Input Rise & Fall Times, t <sub>r</sub> , t <sub>f</sub>	.....	Max 500 ns

\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)

**DC ELECTRICAL CHARACTERISTICS (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)**

Characteristic	Symbol	Test Conditions	T <sub>a</sub> = 25°C		KS74AHCT T <sub>a</sub> = -40°C to +85°C	KS54AHCT T <sub>a</sub> = -55°C to +125°C	Unit
			Typ	Guaranteed Limits			
Minimum High-Level Input Voltage	V <sub>IH</sub>			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V <sub>IL</sub>			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =-20μA I <sub>O</sub> =-6mA	V <sub>CC</sub> 4.2	V <sub>CC</sub> -0.1 3.98	V <sub>CC</sub> -0.1 3.84	V <sub>CC</sub> -0.1 3.7	V
Maximum Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> I <sub>O</sub> =20μA I <sub>O</sub> =12mA I <sub>O</sub> =24mA	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I <sub>IN</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND		±0.1	±1.0	±1.0	μA
Maximum 3-State Leakage Current	I <sub>OZ</sub>	Output Enable =V <sub>IH</sub> V <sub>OUT</sub> =V <sub>CC</sub> or GND		±0.5	±5.0	±10.0	μA
Maximum Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI <sub>CC</sub>	per input pin V <sub>I</sub> =2.4V other Inputs: at V <sub>CC</sub> or GND I <sub>OUT</sub> =0μA		2.7	2.9	3.0	mA



SAMSUNG SEMICONDUCTOR

**KS54AHCT 564  
KS74AHCT****Octal D-Type Flip-Flops  
with 3-State Outputs**

T-46-07-05

**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r$ ,  $t_f < 2\text{ ns}$ ), AHCT564

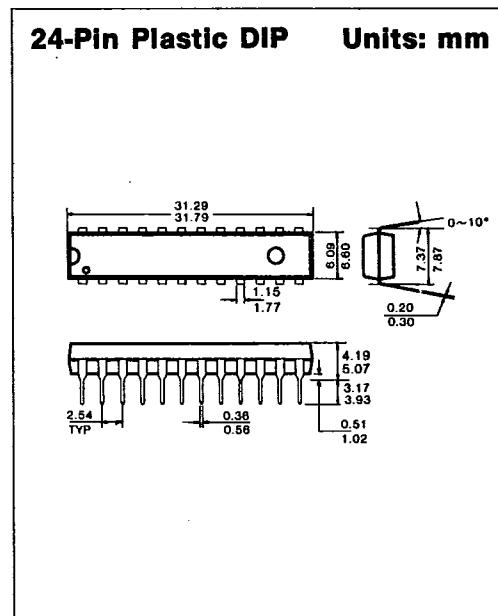
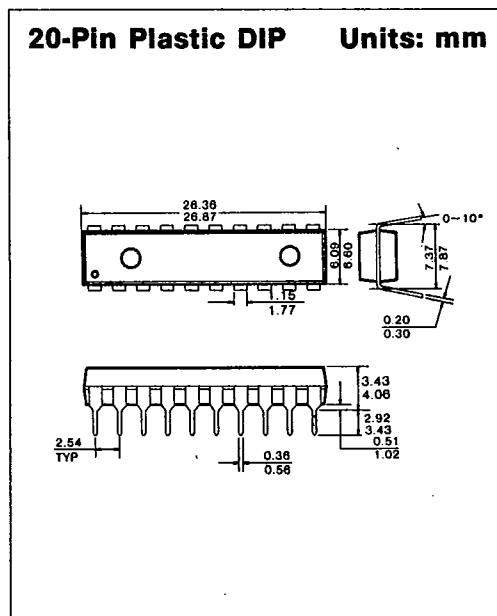
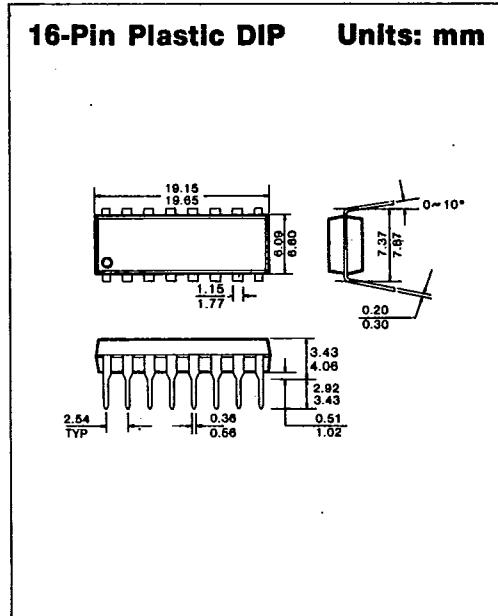
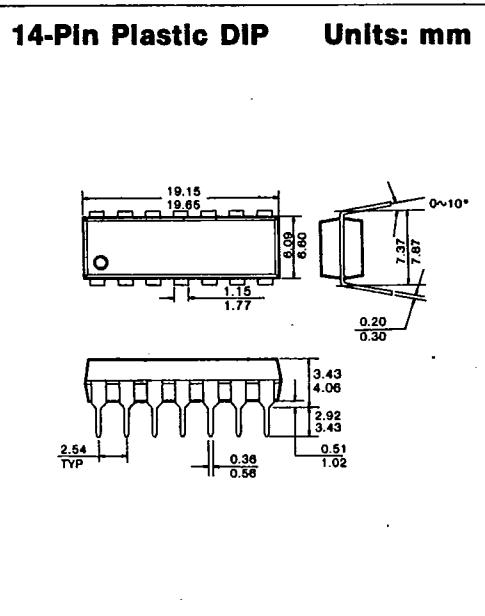
Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$	KS74AHCT		KS54AHCT		Unit
			$V_{cc} = 5.0\text{V}$	Typ	Min	Max	Min	
Maximum Operating Frequency	$f_{max}$	$C_L = 50\text{pF}$	50	35			30	
Propagation Delay, CLK to any $\bar{Q}$	$t_{PLH}$	$C_L = 50\text{pF}$	8		14		17	ns
		$C_L = 150\text{pF}$	11		19		23	
Output Enable Time, $\bar{OC}$ to any $\bar{Q}$	$t_{PHL}$	$C_L = 50\text{pF}$	8		14		17	ns
		$C_L = 150\text{pF}$	11		19		23	
Output Disable Time, $\bar{OC}$ to any $\bar{Q}$	$t_{PZH}$	$R_L = 1\text{k}\Omega$	11		18		22	ns
		$C_L = 150\text{pF}$	14		23		28	
Pulse Width, CLK High or Low	$t_{PLZ}$	$C_L = 50\text{pF}$	11		18		22	ns
		$C_L = 150\text{pF}$	14		23		28	
Setup Time, D before CLK†	$t_{su}$		9	15		18		ns
Hold Time, D after CLK†	$t_h$		-3	0		0		ns
Input Capacitance	$C_{IN}$		5					pF
Output Capacitance	$C_{OUT}$	Output Disabled	10					pF
Power Dissipation Capacitance* (per stage)	$C_{PD}$	$\bar{OC} = V_{cc}$	5					pF
		$\bar{OC} = \text{GND}$	30					

\*  $C_{PD}$  determines the no-load dynamic power dissipation:  $P_D = C_{PD} V_{cc}^2 f + I_{cc} V_{cc}$ .

† For AC switching test circuits and timing waveforms see section 2.



SAMSUNG SEMICONDUCTOR

**PACKAGE DIMENSIONS**T-90-20**1. PLASTIC PACKAGES**

7

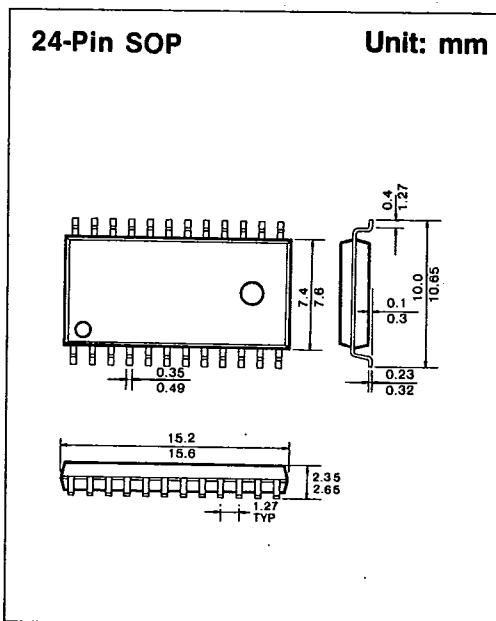
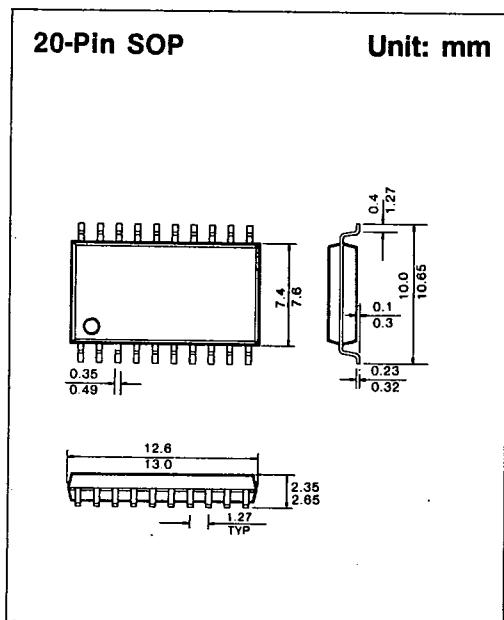
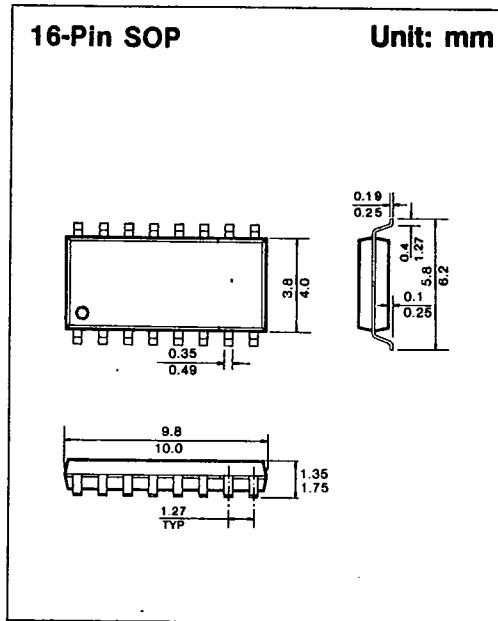
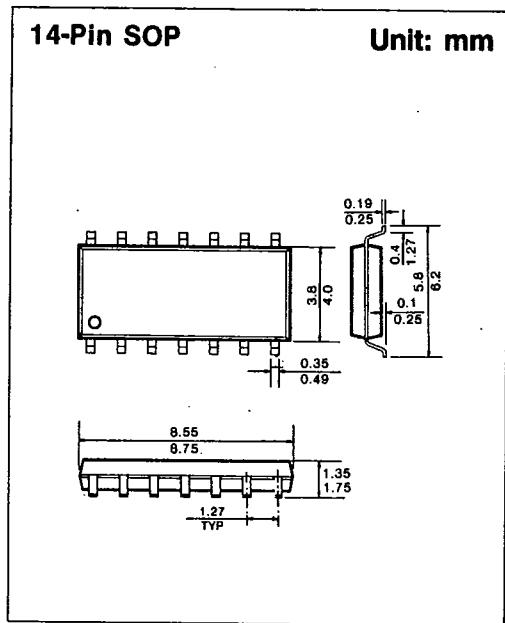


SAMSUNG SEMICONDUCTOR

1675

A-04

781

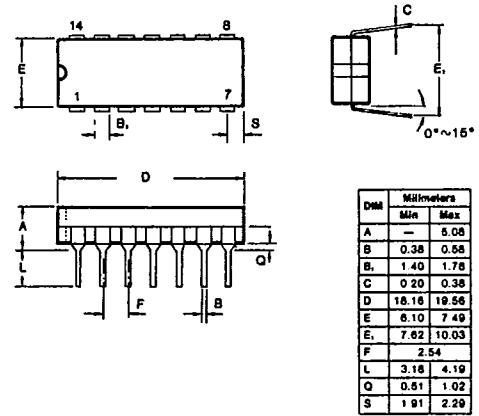
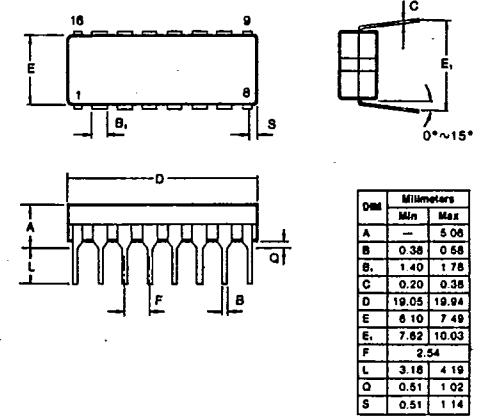
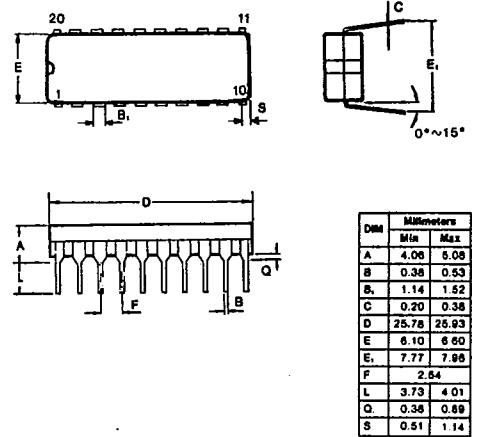
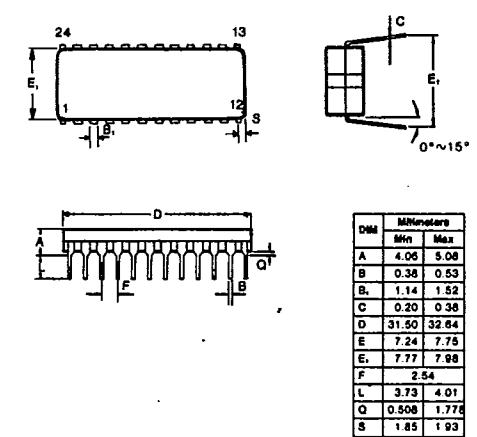
**PACKAGE DIMENSIONS****T-90-20**

SAMSUNG SEMICONDUCTOR

1676

A-05

782

**PACKAGE DIMENSIONS**T-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

7